



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



HiPerFRED

$$V_{RRM} = 1200V$$

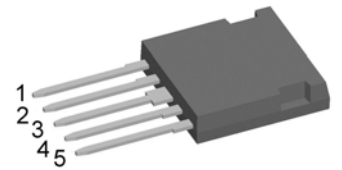
$$I_{DAV} = 30A$$

$$t_{rr} = 40ns$$


High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 3~ Rectifier Bridge

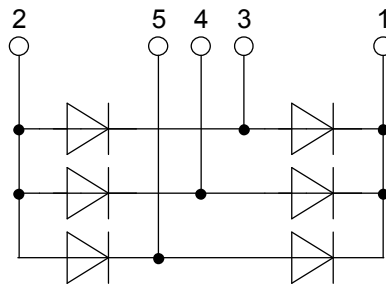
Part number

FUE30-12N1



Backside: isolated

 E72873

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

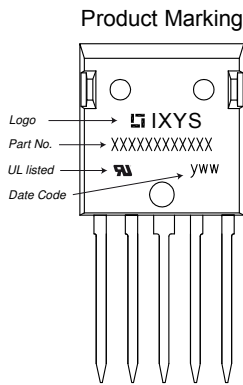
- Rectifiers in switch mode power supplies (SMPS)

Package: i4-Pac

- Isolation Voltage: 3000V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1200	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current, drain current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^\circ\text{C}$			100	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^\circ\text{C}$			0.5	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^\circ\text{C}$			2.37	V
						3.17	V
		$I_F = 30\text{ A}$	$T_{VJ} = 150^\circ\text{C}$			1.60	V
						2.54	V
I_{DAV}	bridge output current	$T_C = 120^\circ\text{C}$ rectangular $d = 1/3$	$T_{VJ} = 175^\circ\text{C}$			30	A
V_{FO}	threshold voltage	} for power loss calculation only				0.97	V
r_F	slope resistance					48	m Ω
R_{thJC}	thermal resistance junction to case					2.3	K/W
R_{thCH}	thermal resistance case to heatsink				0.20		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		65	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		90	A
C_J	junction capacitance	$V_R = 600\text{ V}$ $f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		5	pF
I_{RM}	max. reverse recovery current	} $I_F = 15\text{ A}; V_R = 600\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		6	A
				$T_{VJ} = 100^\circ\text{C}$		9	A
t_{rr}	reverse recovery time	} $-di_F/dt = 200\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$		50	ns
				$T_{VJ} = 100^\circ\text{C}$		140	ns

Package i4-Pac		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			50	A
T_{stg}	storage temperature		-55		150	°C
T_{VJ}	virtual junction temperature		-55		175	°C
Weight				9		g
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/Apb}$		terminal to backside	5.1			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

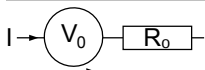


Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FUE30-12N1	FUE30-12N1	Tube	25	488690

Equivalent Circuits for Simulation

* on die level

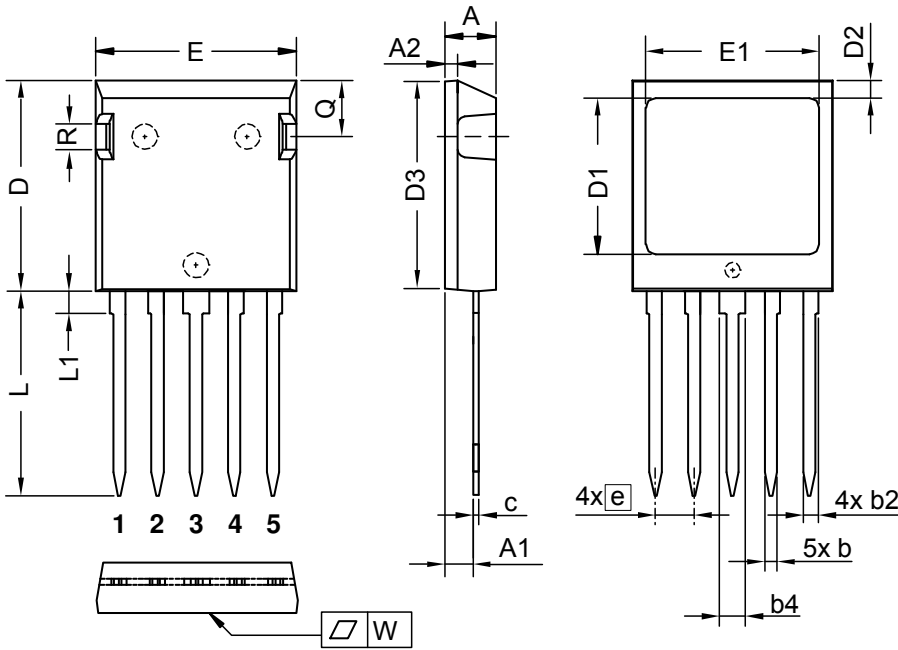
$T_{VJ} = 175\text{ °C}$



Fast Diode

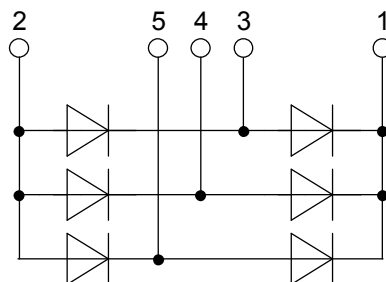
$V_{0\ max}$	threshold voltage	0.97	V
$R_{0\ max}$	slope resistance *	46	mΩ

Outlines i4-Pac



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81 BSC		0.150 BSC	
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convexbow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side



Fast Diode

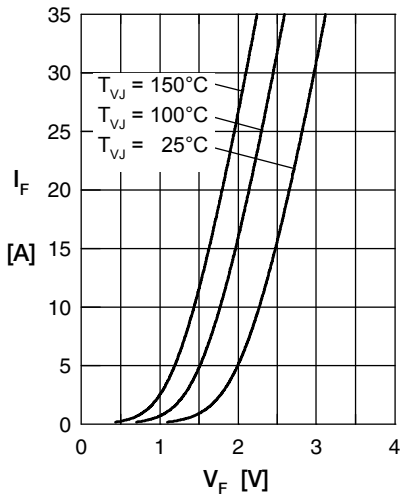


Fig. 1 Forward current I_F versus V_F

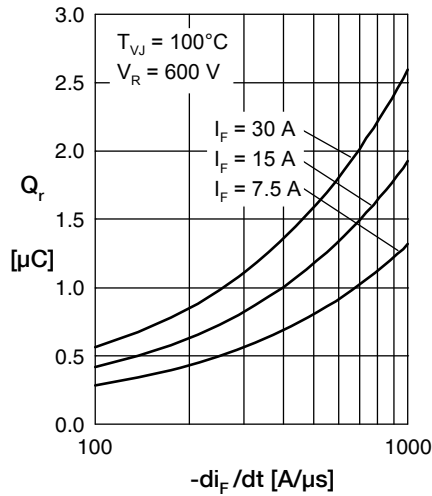


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

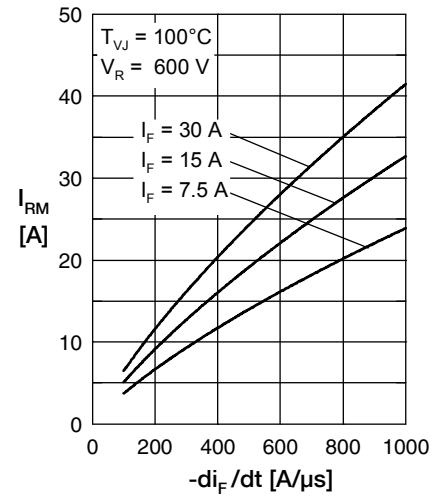


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

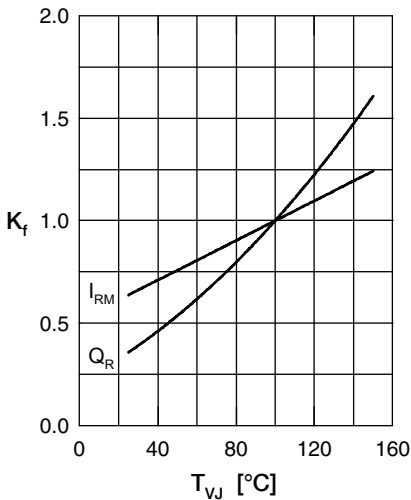


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

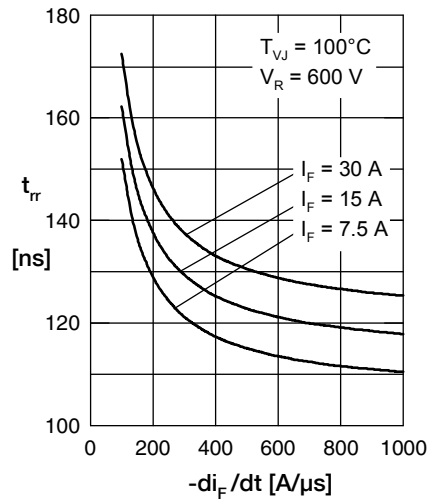


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

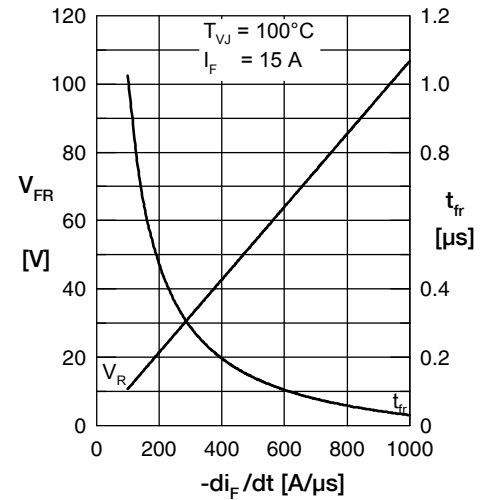


Fig. 6 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt

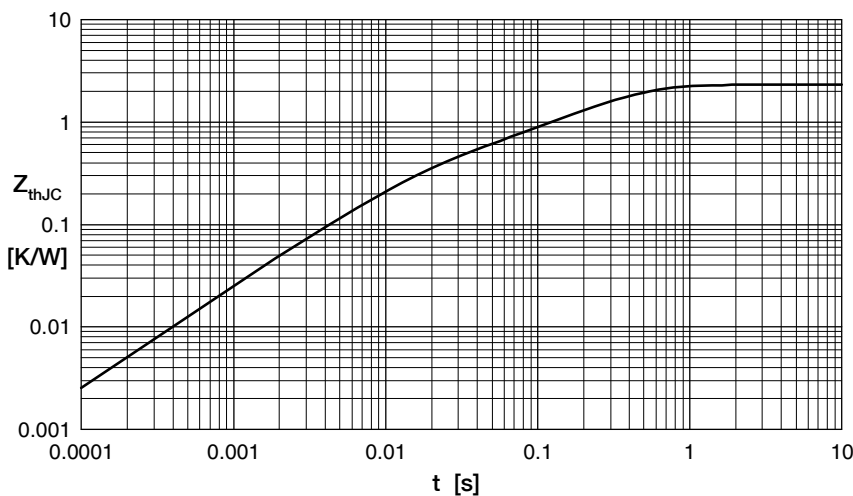


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.78545	0.0052
2	0.30245	0.0003
3	0.0621	0.0004
4	1.15	0.0092